2-input NAND Gate

HITACHI

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Description

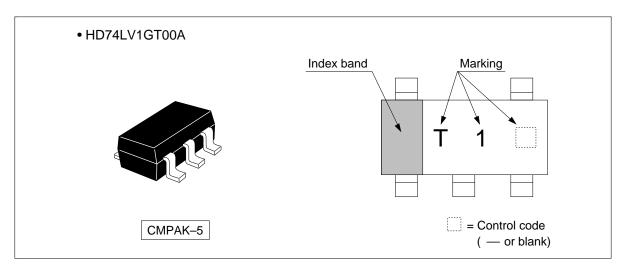
The HD74LV1GT00A is high speed CMOS two input NAND gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output. Low voltage and high speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- TTL compatible input level.
 Supply voltage range: 4.5 to 5.5 V
 Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V) All outputs V_{O} (Max.) = 5.5 V (@ V_{CC} = 0 V)
- Output current $\pm 12 \text{ mA}$ (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.



Outline and Article Indication

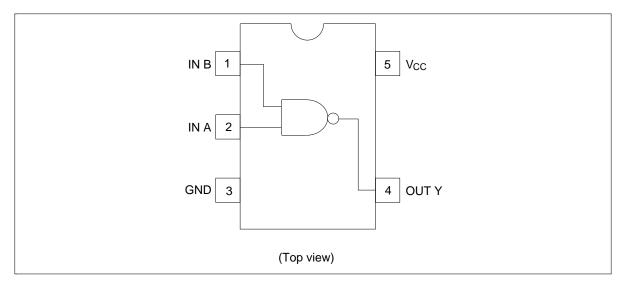


Function Table

Inputs		Output Y			
A	В				
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			

H : High level L : Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage	V _{cc}	-0.5 to 7.0	V	
Input voltage	V _{IN}	-0.5 to 7.0	V	
Output voltage	V_{OUT}	-0.5 to V_{cc} + 0.5	V	Output : H or L
		-0.5 to 7.0		V _{cc} : OFF
Input diode current	I _{IK}	-20	mA	
Output diode current	I _{OK}	±50	mA	
Output current	I _{OUT}	±25	mA	
V _{cc} , GND current	I _{CC} or I _{GND}	±50	mA	
Power dissipation	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Recommended Operating Conditions

Item	Symbol	Ratings	Unit
Supply voltage	V _{cc}	4.5 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V_{OUT}	0 to V _{cc}	V
Operating temperature	T _{opr}	-40 to +85	°C
Input rise / fall time	t _r , t _f	0 to 20 (V _{CC} = 4.5 to 5.5 V)	ns

Electrical Characteristic

• $Ta = -40 \text{ to } 85^{\circ}C$

Item	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
Input voltage	V_{IH}	4.5 to 5.5	2.0	_	_	V	
	V _{IL}	4.5 to 5.5	_		0.8		
Hysteresis voltage	V _H	5.0	_	0.15	_	V	$V_T^+ - V_T^-$
Output voltage	V _{OH}	Min to Max	V _{cc} -0.1			V	I _{OH} = -50 μA
		4.5	3.8		_	_	I _{OH} = -12 mA
	V _{OL}	Min to Max	_	_	0.1	_	$I_{OL} = 50 \mu A$
		4.5			0.55	_	I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_		±1	μΑ	V _{IN} = 5.5 V or GND
Quiescent supply current	I _{cc}	5.5	_	_	10	μΑ	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
	ΔI_{CC}	5.5	_	_	1.5	mA	One input $V_{IN} = 3.4 \text{ V}$, other input V_{CC} or GND
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V _o = 5.5 V
Input capacitance	C _{IN}	5.0	_	2.5	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

•
$$V_{CC} = 5.0 \pm 0.5 \text{ V}$$

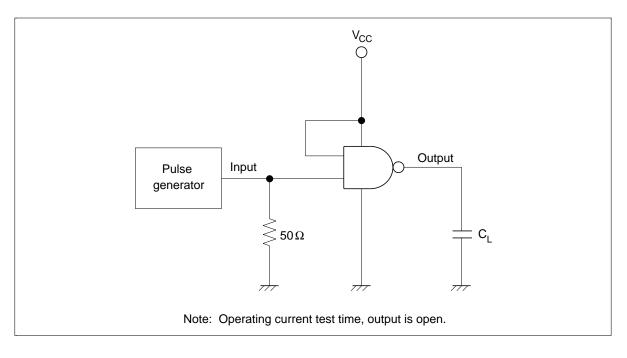
Item	Symbol	$T_a = 2$	$T_a = 25^{\circ}C$ $T_a = -40 \text{ to } 85^{\circ}C$		Unit	Test	FROM	ТО		
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}		5.0	6.9	1.0	8.0	ns	C _L = 15 pF	A or B	Υ
delay time	$t_{\tiny PHL}$	_	5.5	7.9	1.0	9.0	_	$C_L = 50 pF$	_	

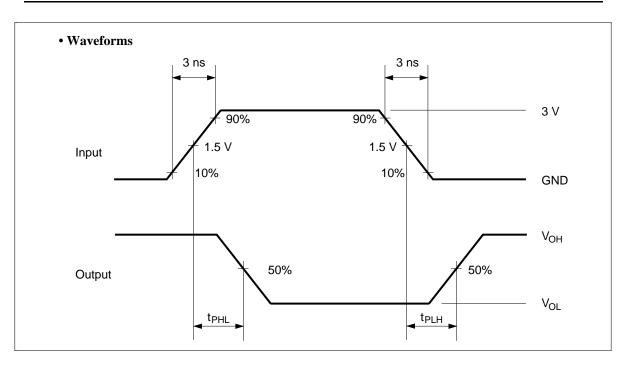
Operating Characteristics

•
$$C_L = 50 pF$$

Item	Symbol	V _{cc} (V)	$T_a = 25^{\circ}C$			Unit	Test Conditions	
			Min	Тур	Max	<u> </u>		
Power dissipation capacitance	C_{PD}	5.0	_	11.0	_	pF	f = 10 MHz	

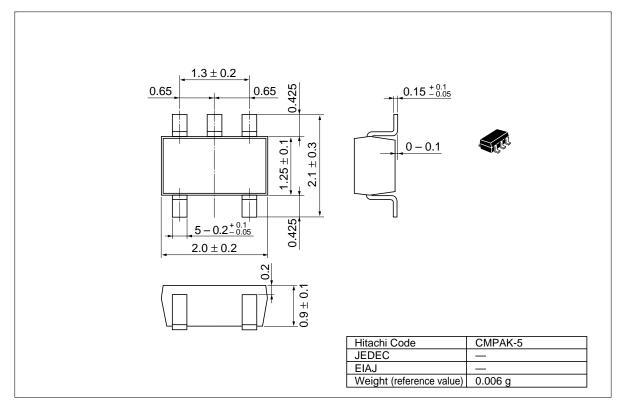
Test Circuit





Package Dimensions

Unit: mm



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